CEL

PHOTOCOUPLER
PS2703-1

HIGH ISOLATION VOLTAGE
HIGH COLLECTOR TO EMITTER VOLTAGE TYPE
SOP MULTI PHOTOCOUPLER

–NEPOC Series–

DESCRIPTION

The PS2703-1 is an optically coupled isolator containing a GaAs light emitting diode and an NPN silicon phototransistor.

This is mounted in a plastic SOP (Small Outline Package) for high density applications.

This package has shield effect to cut off ambient light.

FEATURES

- High isolation voltage (BV = 3 750 Vr.m.s.)
- High collector to emitter voltage (V_{CEO} = 120 V)
- SOP (Small Outline Package) type
- Each isolated channel per package
- High-speed switching (t_r, t_f = 10 μs TYP.)
- Taping product number: PS2703-1-F3, F4
- UL approved: File No. E72422 (S)
- VDE0884 approved (Option)

APPLICATIONS

- Hibrid IC
- Telephone/FAX
- FA/OA equipment
- Programmable logic controllers
- Power supply

ORDERING INFORMATION (Solder Contains Lead)

Part Number	Package	Safety Standard Approval
PS2703-1	4-pin SOP	Standard specification products • UL approved
PS2703-1-V	4-pin SOP	VDE0884 specification products (Option)

ORDERING INFORMATION (Pb-Free)

Part Number	Package	Safety Standard Approval
PS2703-1-A	4-pin SOP	Standard specification products • UL approved
PS2703-1-V-A	4-pin SOP	VDE0884 specification products (Option)

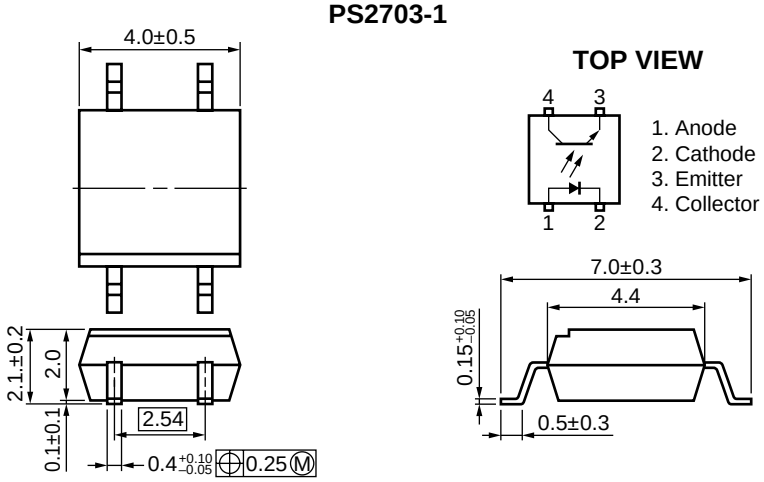
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Document No. PN10242EJ01V0DS (1st edition)
(Previous No. P11308EJ6V0DS00)
Date Published February 2003 CP(K)

The mark ★ shows major revised points.

★ **PACKAGE DIMENSIONS (in millimeters)**

PS2703-1



ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise specified)

Parameter		Symbol	Ratings	Unit
Diode	Forward Current (DC)	I_F	50	mA
	Reverse Voltage	V_R	6	V
	Power Dissipation Derating	ΔP_D/°C	0.8	mW/°C
	Power Dissipation	P_D	80	mW
	Peak Forward Current*1	I_{FP}	1	A
Transistor	Collector to Emitter Voltage	V_{CEO}	120	V
	Emitter to Collector Voltage	V_{ECO}	6	V
	Collector Current	I_C	30	mA
	Power Dissipation Derating	ΔP_C/°C	1.5	mW/°C
	Power Dissipation	P_C	150	mW
Isolation Voltage*2		BV	3 750	Vr.m.s.
Operating Ambient Temperature		T_A	–55 to +100	°C
Storage Temperature		T_{stg}	–55 to +150	°C

***1** PW = 100 μs, Duty Cycle = 1 %

***2** AC voltage for 1 minute at T_A = 25 °C, RH = 60 % between input and output

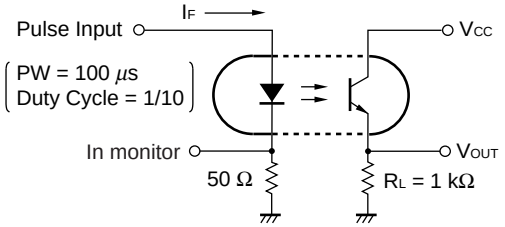
ELECTRICAL CHARACTERISTICS (T_A = 25 °C)

Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Diode	Forward Voltage	V_F	I_F = 5 mA		1.1	1.4	V
	Reverse Current	I_R	V_R = 5 V			5	μA
	Terminal Capacitance	C_t	V = 0 V, f = 1 MHz		30		pF
Transistor	Collector to Emitter Dark Current	I_{CEO}	I_F = 0 mA, V_{CE} = 120 V			100	nA
Coupled	Current Transfer Ratio (I_C/I_F)*1	CTR	I_F = 5 mA, V_{CE} = 5 V	50	150	400	%
			I_F = 1 mA, V_{CE} = 5 V	10	80		
	Collector Saturation Voltage	$V_{CE (sat)}$	I_F = 10 mA, I_C = 2 mA			0.3	V
	Isolation Resistance	R_{I-O}	V_{I-O} = 1 kV_{DC}	10^{11}			Ω
	Isolation Capacitance	C_{I-O}	V = 0 V, f = 1 MHz		0.4		pF
	Rise Time *2	t_r	V_{CC} = 5 V, I_C = 2 mA, R_L = 1 kΩ		10		μs
	Fall Time *2	t_f			10		

***1** CTR rank

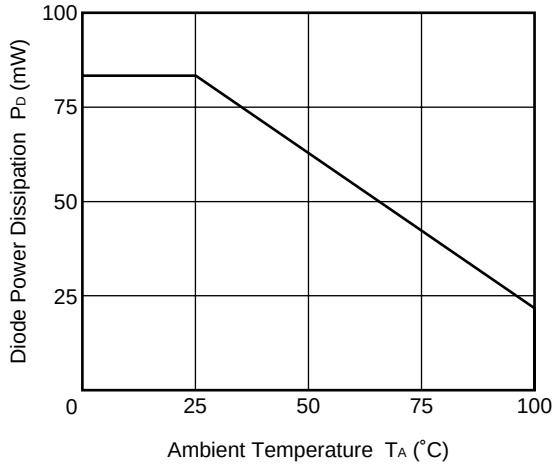
CTR rank	CTR (%)	Conditions
K	200 to 400	I_F = 5 mA, V_{CE} = 5 V
	80 to	I_F = 1 mA, V_{CE} = 5 V
L	100 to 300	I_F = 5 mA, V_{CE} = 5 V
	25 to	I_F = 1 mA, V_{CE} = 5 V
M	50 to 150	I_F = 5 mA, V_{CE} = 5 V
	10 to	I_F = 1 mA, V_{CE} = 5 V

***2** Test circuit for switching time

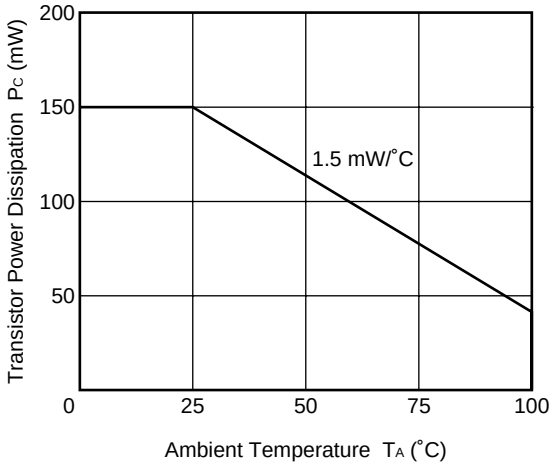


★ TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise specified)

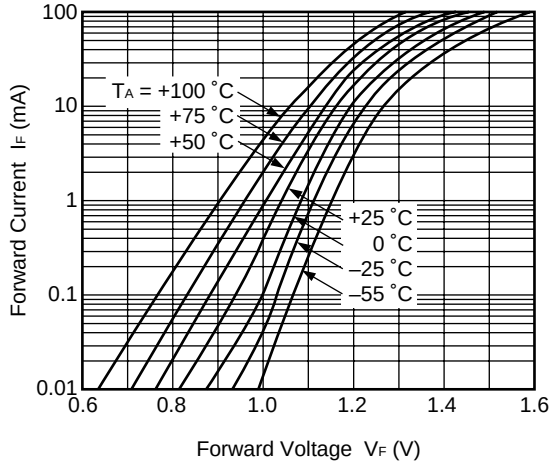
DIODE POWER DISSIPATION vs. AMBIENT TEMPERATURE



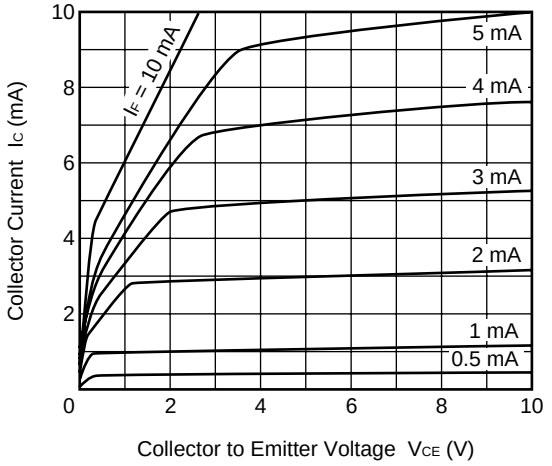
TRANSISTOR POWER DISSIPATION vs. AMBIENT TEMPERATURE



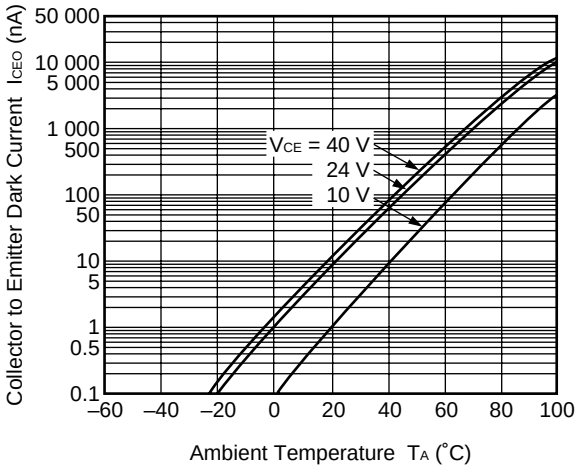
FORWARD CURRENT vs. FORWARD VOLTAGE



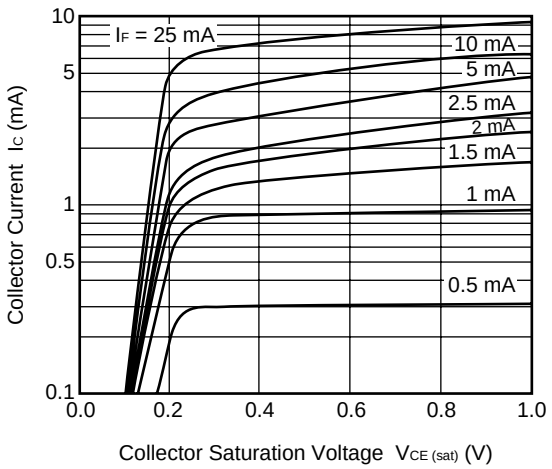
COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE



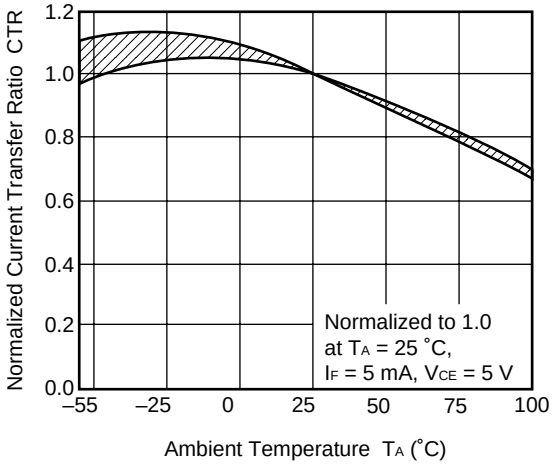
COLLECTOR TO EMITTER DARK CURRENT vs. AMBIENT TEMPERATURE



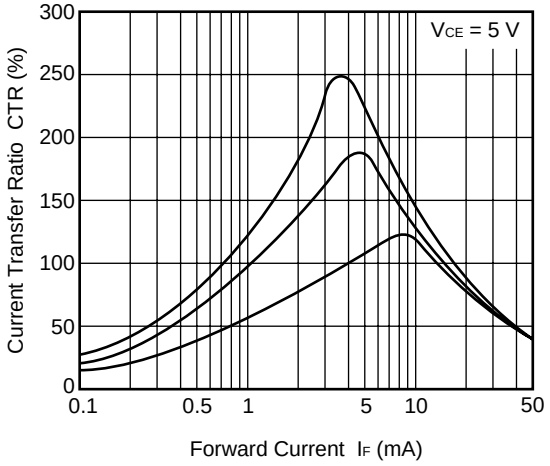
COLLECTOR CURRENT vs. COLLECTOR SATURATION VOLTAGE



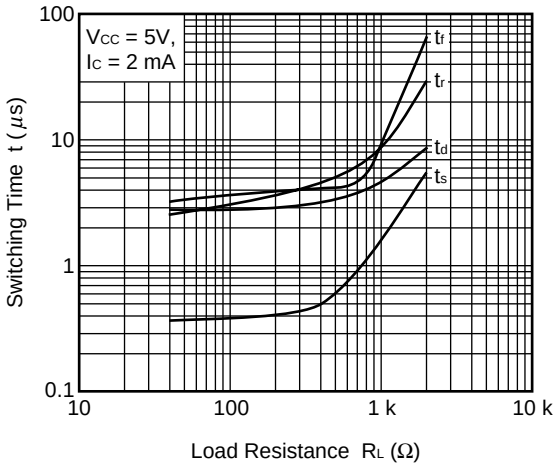
NORMALIZED CURRENT TRANSFER RATIO vs. AMBIENT TEMPERATURE



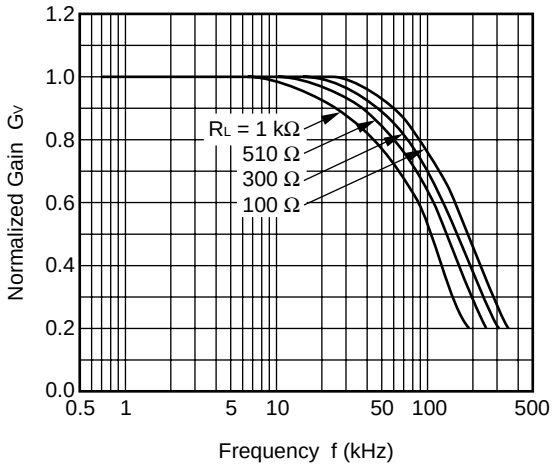
CURRENT TRANSFER RATIO vs. FORWARD CURRENT



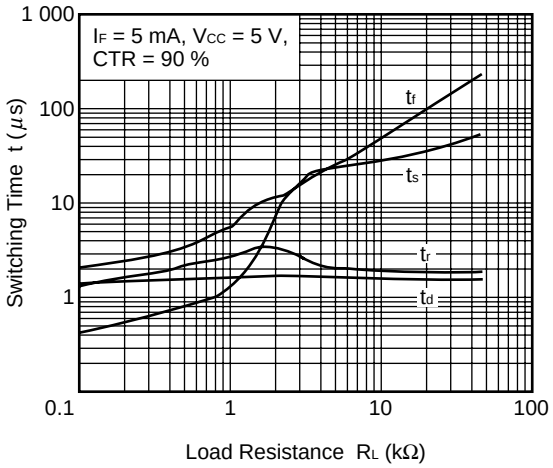
SWITCHING TIME vs. LOAD RESISTANCE



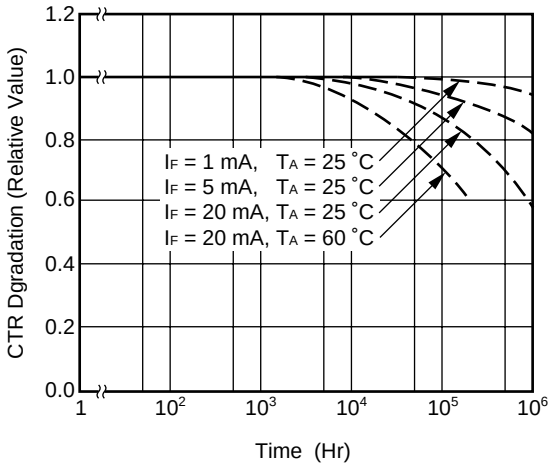
FREQUENCY RESPONSE



SWITCHING TIME vs. LOAD RESISTANCE



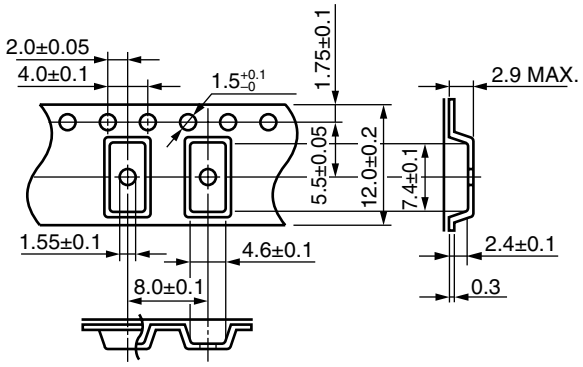
LONG TIME CTR DEGRADATION



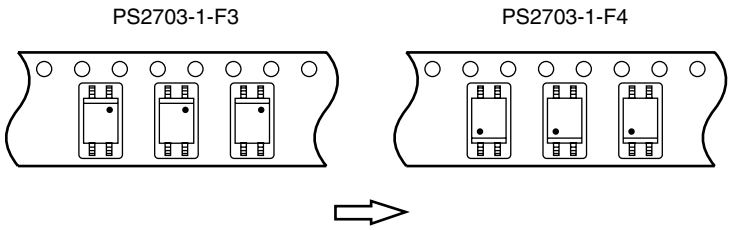
Remark The graphs indicate nominal characteristics.

★ **TAPING SPECIFICATIONS (in millimeters)**

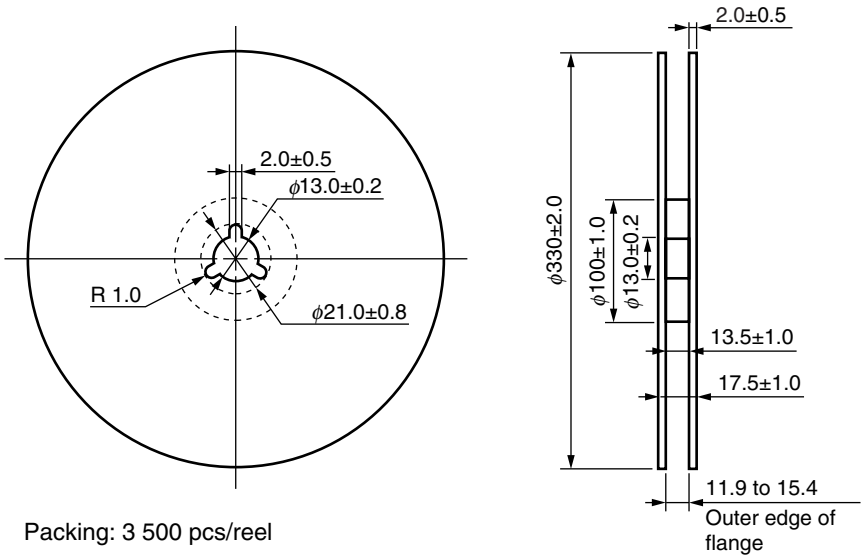
Outline and Dimensions (Tape)



Tape Direction



Outline and Dimensions (Reel)



Packing: 3 500 pcs/reel

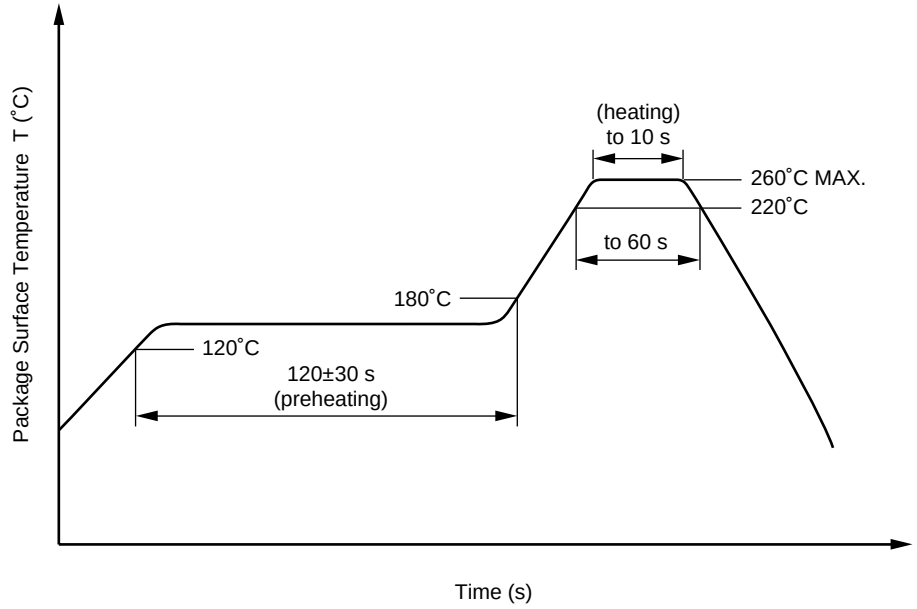
★ NOTES ON HANDLING

1. Recommended soldering conditions

(1) Infrared reflow soldering

• Peak reflow temperature	260°C or below (package surface temperature)
• Time of peak reflow temperature	10 seconds or less
• Time of temperature higher than 220°C	60 seconds or less
• Time to preheat temperature from 120 to 180°C	120±30 s
• Number of reflows	Three
• Flux	Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of 0.2 Wt% is recommended.)

Recommended Temperature Profile of Infrared Reflow



(2) Wave soldering

• Temperature	260°C or below (molten solder temperature)
• Time	10 seconds or less
• Preheating conditions	120°C or below (package surface temperature)
• Number of times	One (Allowed to be dipped in solder including plastic mold portion.)
• Flux	Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of 0.2 Wt% is recommended.)

(3) Cautions

• Fluxes

Avoid removing the residual flux with freon-based and chlorine-based cleaning solvent.

2. Cautions regarding noise

Be aware that when voltage is applied suddenly between the photocoupler's input and output or between collector-emitters at startup, the output side may enter the on state, even if the voltage is within the absolute maximum ratings.

★ USAGE CAUTIONS

1. Protect against static electricity when handling.
2. Avoid storage at a high temperature and high humidity.

SPECIFICATION OF VDE MARKS LICENSE DOCUMENT (VDE0884)

Parameter	Symbol	Speck	Unit
Application classification (DIN VDE 0109)			
for rated line voltages ≤ 300 Vr.m.s.		IV	
for rated line voltages ≤ 600 Vr.m.s.		III	
Climatic test class (DIN IEC 68 Teil 1/09.80)		55/100/21	
Dielectric strength maximum operating isolation voltage.			
Test voltage (partial discharge test procedure a for type test and random test)	U_{IORM}	710	V_{peak}
$U_{pr} = 1.2 \times U_{IORM}$, $P_d < 5$ pC	U_{pr}	850	V_{peak}
★ Test voltage (partial discharge test procedure b for all devices test) $U_{pr} = 1.6 \times U_{IORM}$, $P_d < 5$ pC	U_{pr}	1 140	V_{peak}
Highest permissible overvoltage	U_{TR}	6 000	V_{peak}
Degree of pollution (DIN VDE 0109)		2	
Clearance distance		> 5	mm
Creepage distance		> 5	mm
Comparative tracking index (DIN IEC 112/VDE 0303 part 1)	CTI	175	
Material group (DIN VDE 0109)		III a	
Storage temperature range	T_{stg}	–55 to +150	°C
Operating temperature range	T_A	–55 to +100	°C
Isolation resistance, minimum value			
V_{IO} = 500 V dc at T_A = 25 °C	Ris MIN.	10^{12}	Ω
V_{IO} = 500 V dc at T_A MAX. at least 100 °C	Ris MIN.	10^{11}	Ω
Safety maximum ratings (maximum permissible in case of fault, see thermal derating curve)			
Package temperature	Tsi	150	°C
Current (input current I_F, Psi = 0)	Isi	200	mA
Power (output or total power dissipation)	Psi	300	mW
Isolation resistance			
V_{IO} = 500 V dc at T_A = 175 °C (Tsi)	Ris MIN.	10^9	Ω

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Subject: Compliance with EU Directives

CEL certifies, to its knowledge, that semiconductor and laser products detailed below are compliant with the requirements of European Union (EU) Directive 2002/95/EC Restriction on Use of Hazardous Substances in electrical and electronic equipment (RoHS) and the requirements of EU Directive 2003/11/EC Restriction on Penta and Octa BDE.

CEL Pb-free products have the same base part number with a suffix added. The suffix –A indicates that the device is Pb-free. The –AZ suffix is used to designate devices containing Pb which are exempted from the requirement of RoHS directive (*). In all cases the devices have Pb-free terminals. All devices with these suffixes meet the requirements of the RoHS directive.

This status is based on CEL's understanding of the EU Directives and knowledge of the materials that go into its products as of the date of disclosure of this information.

Restricted Substance per RoHS	Concentration Limit per RoHS (values are not yet fixed)	Concentration contained in CEL devices	
Lead (Pb)	< 1000 PPM	-A	-AZ
		Not Detected	(*)
Mercury	< 1000 PPM	Not Detected	
Cadmium	< 100 PPM	Not Detected	
Hexavalent Chromium	< 1000 PPM	Not Detected	
PBB	< 1000 PPM	Not Detected	
PBDE	< 1000 PPM	Not Detected	

If you should have any additional questions regarding our devices and compliance to environmental standards, please do not hesitate to contact your local representative.

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